



PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#5/5-15-02
Pre-Amendment
5-15-02
Gao

In re application of

Yoji OKAZAKI, et al.

Appln. No.: 09/987,049

Confirmation No.: 6352

Group Art Unit: Not Assigned

Filed: November 13, 2001

Examiner: Not Assigned

For: COLOR LASER DISPLAY APPARATUS HAVING FLUORESCENT SCREEN
SCANNED WITH MODULATED ULTRAVIOLET LASER LIGHT

PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Sir:

Prior to examination, please amend the above-identified application as follows:

IN THE SPECIFICATION:

Page 26, last paragraph bridging page 27, delete and insert the following:

Figure 14 shows an example of a layering structure of a gallium nitride semiconductor laser having a broad area emission range, listed as 1) above. In the gallium nitride semiconductor laser having this layering structure, an n-type $\text{Ga}_{1-z1}\text{Al}_{z1}\text{N}/\text{GaN}$ super lattice cladding layer 102 ($0.05 < z1 < 1$), an n-type or i-type GaN optical waveguide layer 104, an $\text{In}_{1-z2}\text{Ga}_{z2}\text{N}$ (doped with Si)/ $\text{In}_{1-z3}\text{Ga}_{z3}\text{N}$ multiple quantum well active layer 106 ($0.01 < z2 < 0.05$, $0.1 < z3 < 0.3$), a p-type $\text{Ga}_{0.8}\text{Al}_{0.2}\text{N}$ carrier blocking layer 108, an n-type or i-type GaN photoconductive layer 110, a p-type $\text{Ga}_{1-z1}\text{Al}_{z1}\text{N}/\text{GaN}$ super lattice cladding layer 112, and a p-type GaN contact layer are sequentially layered on an n-type GaN (0001) substrate 100. An insulating film 116 is formed on the p-type GaN contact layer excepting a stripe region with a

Al
cont